

IN THE CLAIMS:

Claims 6 and 7 are currently pending in this application, while all remaining pending claims are being withdrawn from further consideration without prejudice or disclaimer, as follows:

1. (Withdrawn) A semiconductor integrated circuit device including a gate electrode structure comprising at least:
 - a first conductive region and a second conductive region formed on a semiconductor substrate and separated by an isolation region;
 - a gate insulator formed on said first conductive region and second conductive region across said isolation region;
 - a second conductive silicon layer, which is deposited on said first conductive region, and a first conductive silicon layer, which is deposited on said second conductive region, and formed on said gate insulator having a boundary on said isolation region;
 - a first nitride film of refractory metal, which is formed on said first conductive and second conductive silicon layers and separated at a boundary of said first conductive and second conductive silicon layers; and
 - a first refractory metal film, which is formed on said first nitride film of refractory metal and separated at a boundary of said first conductive and second conductive silicon layers.
2. (Withdrawn) A semiconductor integrated circuit device according to claim 1, wherein said first conductive and second conductive silicon layers are also separated.
3. (Withdrawn) A semiconductor integrated circuit device according to claim 1, wherein a second refractory metal or a second nitride film of refractory metal is embedded in said regions separating first nitride film of refractory metal and first refractory metal.
4. (Withdrawn) A semiconductor integrated circuit device according to claim 1, wherein:
 - an insulator is embedded in said regions separating first nitride film of refractory metal and first refractory metal, and

a layer which comprises one type of film selected from titanium nitride, zirconium nitride, and hafnium nitride or a composite film therefrom is formed on said embedded insulator and said first refractory metal.

5. (Withdrawn) A semiconductor integrated circuit device according to claim 1, wherein a first silicide film of refractory metal is formed between said first nitride film of refractory metal and both of said first conductive and second conductive silicon layers.
6. (Original) A semiconductor integrated circuit device comprising:
 - a first conductive region and a second conductive region formed on a semiconductor substrate and separated by an isolation region;
 - a gate insulator formed on said first conductive region and second conductive region across said isolation region;
 - a second conductive silicon layer which is deposited on said first conductive region, and a first conductive silicon layer which is deposited on said second conductive region, and formed on said gate insulator having a boundary on said isolation region; and
 - carbon which is included in said first nitride film of refractory metal and first refractory metal film on a boundary between said first conductive and second conductive silicon layers in a gate electrode structure consisting of a first nitride film of refractory metal formed on said first conductive and second conductive silicon layers and a first refractory metal film formed on said first nitride film of refractory metal.
7. (Original) A semiconductor integrated circuit device according to claim 6, wherein, instead of carbon, nitrogen and oxygen elements are included in said first nitride film of refractory metal and first refractory metal film on a boundary between said first conductive and second conductive silicon layers.
8. (Withdrawn) A semiconductor integrated circuit device according to claim 6, wherein a first silicide film of refractory metal is formed between said nitride film of refractory material and said first conductive and second conductive silicon layers.

9. (Withdrawn) A semiconductor integrated circuit device according to claim 1, wherein a non-doped silicon layer or germanium-doped silicon layer is formed between said nitride film of refractory material and said first conductive and second conductive silicon layers.
10. (Original) A semiconductor integrated circuit device according to claim 6, wherein a non-doped silicon layer or germanium-doped silicon layer is formed between said first refractory metal silicide and said first conductive and second conductive silicon layers.
- 11-20. (Canceled)
21. (Withdrawn) A semiconductor integrated circuit device according to claim 2, wherein a second refractory metal or a second nitride film of refractory metal is embedded in said isolated region of the first nitride film of refractory metal and the first refractory metal.
22. (Withdrawn) A semiconductor integrated circuit device according to claim 2, wherein:
- an insulator is embedded in said isolated region of said first nitride film of refractory metal and first refractory film, and
 - a layer which comprises one type of film selected from titanium nitride, zirconium nitride, and hafnium nitride or a composite film therefrom is formed on said embedded insulator and said first refractory metal.
23. (Withdrawn) A semiconductor integrated circuit device according to claim 2, wherein a first silicide film of refractory metal is formed between said nitride film of refractory metal and said first and second conductive silicon layers.
24. (Withdrawn) A semiconductor integrated circuit device according to claim 7, wherein a first silicide film of refractory metal is formed between said nitride film of refractory metal and said first and second conductive silicon layers.

25. (Original) A semiconductor integrated circuit device according to claim 6, wherein a non-doped silicon layer or germanium-doped silicon layer is formed between said nitride film of refractory metal and said first and second conductive silicon layers.
26. (Original) A semiconductor integrated circuit device according to claim 8, wherein a non-doped silicon layer or germanium-doped silicon layer is formed between said nitride film of refractory metal and said first and second conductive silicon layers.

27-32 (Canceled)